

NTS580N15P5



N-Channel Enhancement Mode Trench Power MOSFET

Voltage: 150 Volts

Current: 18 Ampers

Package: PDFN5*6

Features

- NH'S Advanced Trench Technology
- Low Rds(on) For Low On-State Loss
- High EAS For High Reliability
- Excellent Qg*Rds(on) Product(FOM)

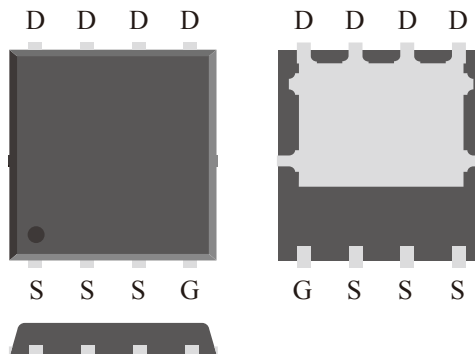
Typical Applications

- DC-DC Converter
- Battery Management System(BMS)
- Printed Circuit Board For Control Circuit
- Uninterruptible Power Supplies(UPS)

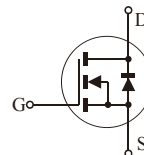
Product Summary

VDS Min.@Tj	150	V
ID Min.@Ta	18	A
RDS(ON)(TYP)@10V	58	mΩ

Diagram:



Polarity:



***100% UIS TESTED**

***100% ΔVDS TESTED**

Absolute Maximum Ratings (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Drain-Source Voltage		V _{DS}	150	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current (Note 1)	Ta= 25 ℃	I _D	18	A
	Ta= 100 ℃		12	
Drain Current-Pulse (Note 1)	Tj< 150 ℃	I _{DM}	72	A
Maximum Power Dissipation Power Dissipation Derating Factor Above 25℃	Ta= 25 ℃	P _D	46	W
	Ta= 100 ℃		19	
Derating Factor		D _F	0.37	W/℃
Avalanche Current,Single Pulse (Note 1)	L= 0.4 mH	I _{AS}	5	A
Single Pulse Avalanche Energy (Note 1) Test Circuit & Waveform See Fig.17	L= 0.4 mH IAS= 5 A, RG= 10.0 Ω Starting Tj=25 ℃, VG = 10.0 V	E _{AS}	5	mJ

Thermal Characteristics (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Typ.	Unit
Junction Temperature		T _J	-55 to 150	℃
Storage Temperature Range		T _{STD}	-55 to 150	℃
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With Ta=25℃	R _{θJA}	55	℃/W
Thermal Resistance Junction-Case With Steady-State	Device Mounted On 1 in2 FR-4 Board With 2oz. Copper	R _{θJC}	2.7	

Notes: 1.Pulse Width Limited By Max. Junction Temperature. (See Fig.14)

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Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Static Off Characteristics						
Drain-Source Breakdown Voltage	VGS=0V,ID=250uA	BV _{DSS}	150	--	--	V
Bvdss Temperature Coefficient	ID=250uA,Reference25℃	ΔBV _{DSS} /ΔT _J	--	0.17	--	V/℃
Drain-Source Leakage Current	VDS= 150 V,VGS=0V	I _{DSS}	--	--	1	uA
Gate-Body Leakage Current	VGS= ±20 V,VDS=0V	I _{GSS}	--	--	±100	nA
Forward Transconductance	ID= 9.0 A,VDS= 5 V	g _{fs}	--	25	--	S
Static On Characteristics						
Gate Threshold Voltage	VGS= VDS ID=250uA	V _{GS(TH)}	1	2	3	V
Drain-Source On Resistance	ID= 9.0 A,VGS= 10.0 V	R _{DS(ON)}	--	58	65	mΩ
	ID= 9.0 A,VGS= 5.0 V		--	70	88	
Dynamic Characteristics						
Gate Resistance	VGS=0V,VDS=0V, Freq.=1MHz	R _g	--	3.9	--	Ω
Input Capacitance	VDS= 50 V	C _{iss}	--	635	--	pF
Output Capacitance	VGS= 0 V	C _{oss}	--	43	--	pF
Reverse Transfer Capacitance	F= 1 MHZ	C _{rss}	--	4.3	--	pF
Switching Paramters With Inductive Load(Test Circuit & Waveform See Fig.15)						
Turn-On Delay Time	VDS= 50 V	t _{d(on)}	--	8	--	ns
Turn-On Rise Time	VGS= 10.0 V	t _r	--	4	--	ns
Turn-Off Delay Time	RG= 10.0 Ω	t _{d(off)}	--	12	--	ns
Turn-Off Rise Time	L= 0.4 mH	t _f	--	3	--	ns
Gate Charge Paramters (Test Circuit & Waveform See Fig.16)						
Total Gate Charge	VDS= 50 V	Q _g	--	8	--	nC
Gate-Source Charge	VGS= 10.0 V	Q _{gs}	--	2	--	nC
Gate-Drain Charge	ID= 18.0 A	Q _{gd}	--	1	--	nC
Drain-Source Diode Characteristics And Maximum Ratings (Test Circuit & Waveform See Fig.18)						
Max. Diode Forward Cuurent		I _S	--	--	18.0	A
Max. Pulsed Forward Cuurent		I _{SM}	--	--	72	A
Diode Forward Voltage	ID= 9.0 A,VGS=0V	V _{SD}	--	0.7	1.2	V
Reverse Recovery Time	IS= 9.0 A,di/dt= 100 A/us	t _{rr}	--	48	--	ns
Reverse Recovery Charge	VGS= 0.0 V	Q _{rr}	--	54	--	nC
Reverse Recovery Current		I _{RRM}	--	2.0	--	A

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Typical Characteristics Curves

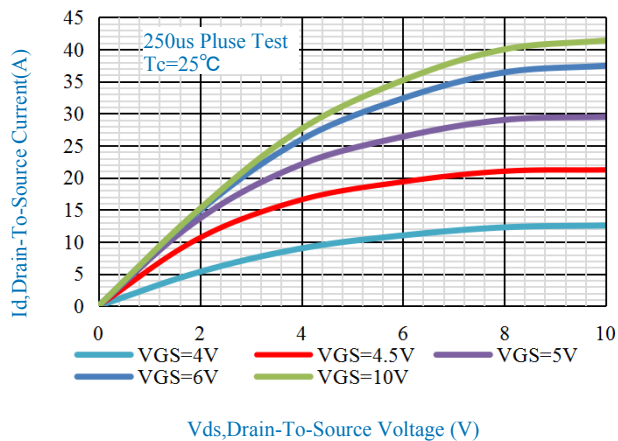


Fig.1-Output Characteristics

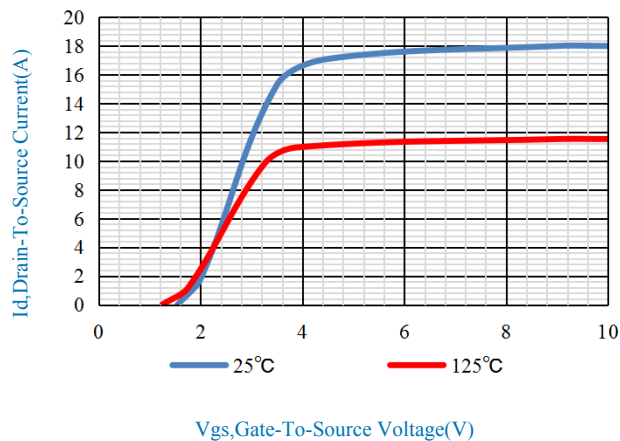


Fig.2-Transfer Characteristics

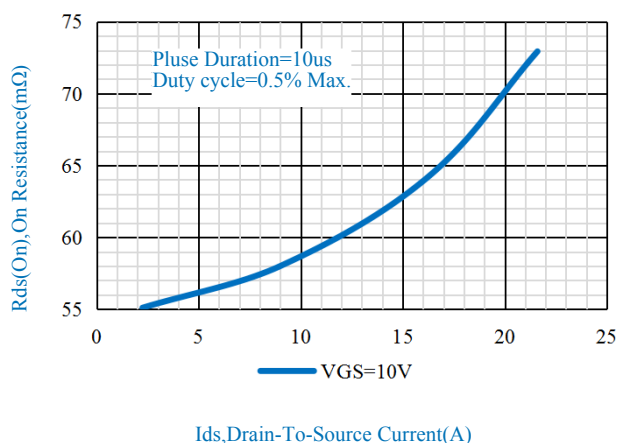


Fig.3-On Resistance Vs. Drain Current

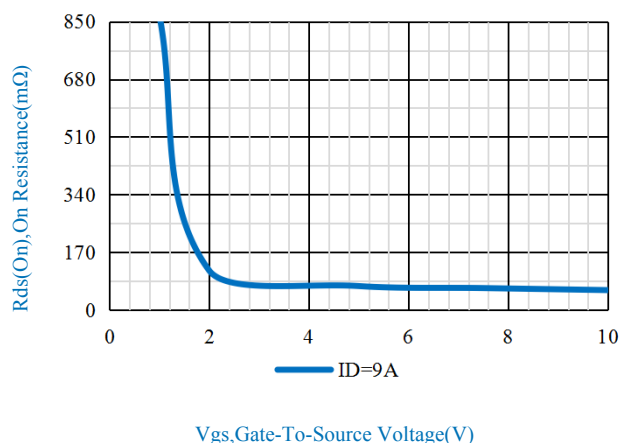


Fig.4-On Resistance Vs. Gate Source Voltage

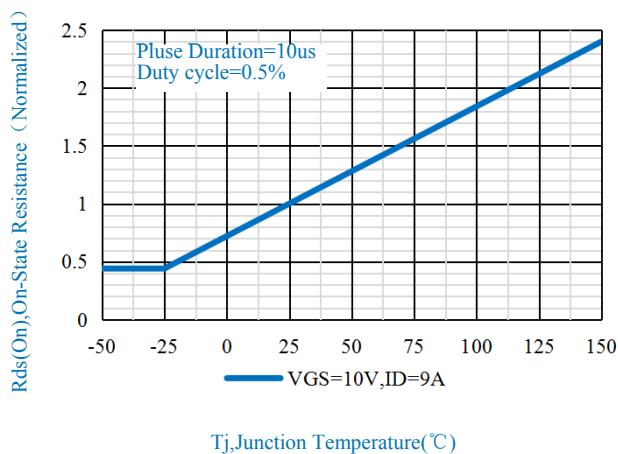


Fig.5-On Resistance Vs. Junction Temperature

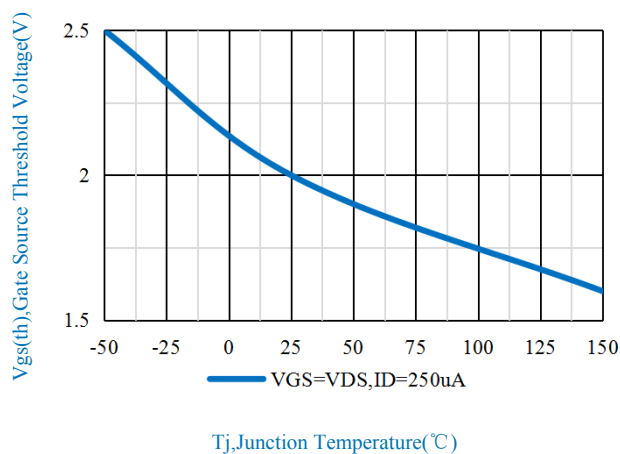


Fig.6-Gate Source Threshold Voltage Vs. Junction Temperature

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Typical Characteristics Curves

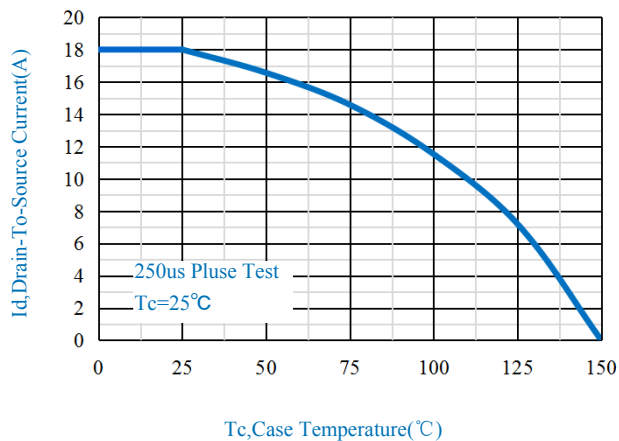


Fig.7-Maximum Continuous Drain Current Vs. Case Temperature

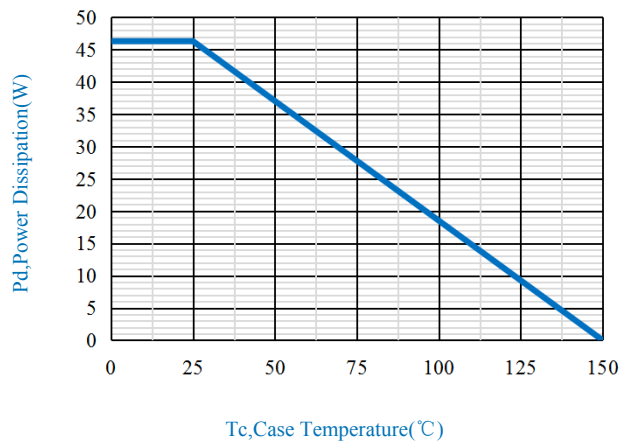


Fig.8-Maximum Power Dissipation Vs. Case Temperature

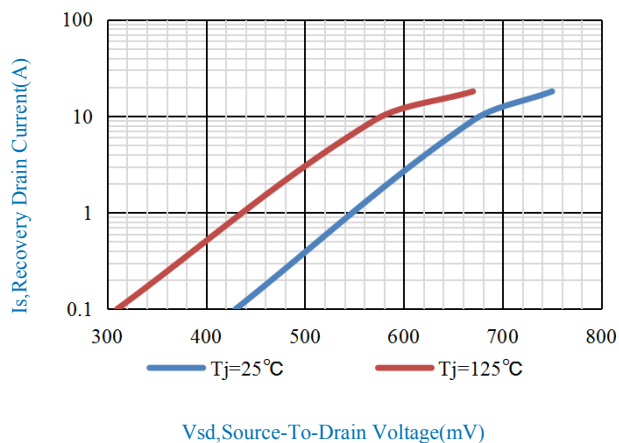


Fig.9-Source-To-Drain Diode Forward Voltage

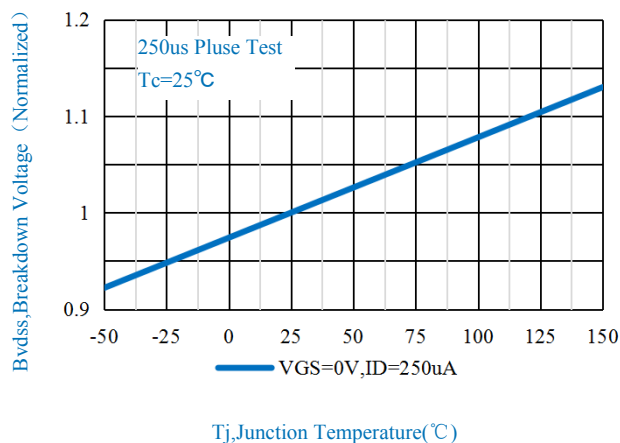


Fig.10-Breakdown Voltage Vs. Junction Temperature

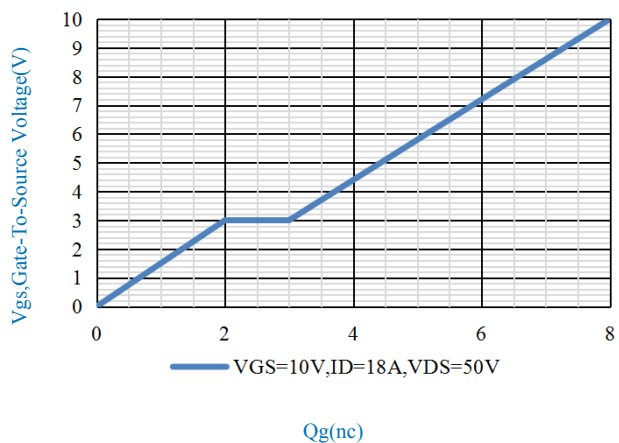


Fig.11-Gate Charge Waveform

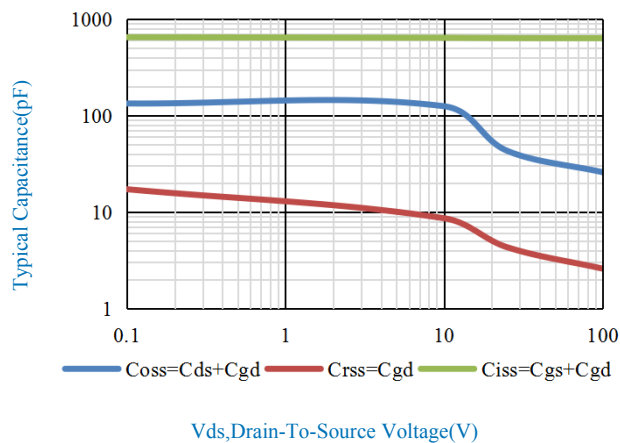


Fig.12-Typical Capacitance Vs. Drain-To-Source Voltage

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Typical Characteristics Curves

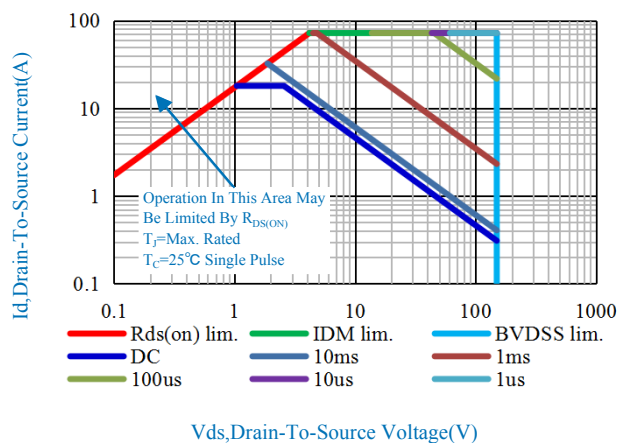


Fig.13-Maximum Safe Operating Area(SOA)

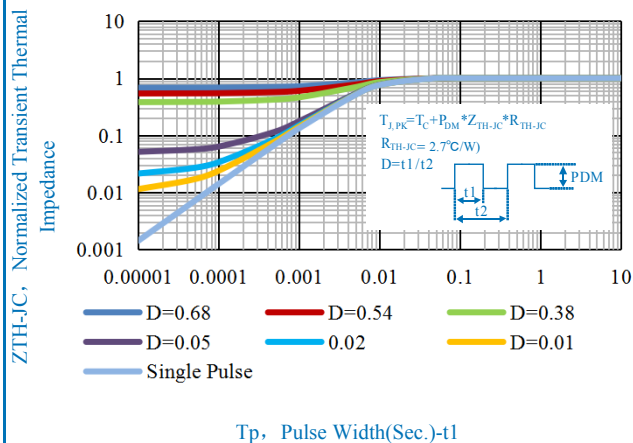


Fig.14- Normalized Maximum Transient Thermal Impedance Vs. Pulse Width

Inductive Load Test Circuit & Waveform

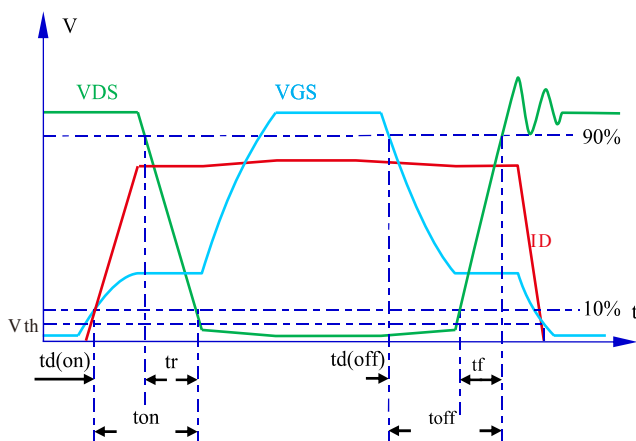
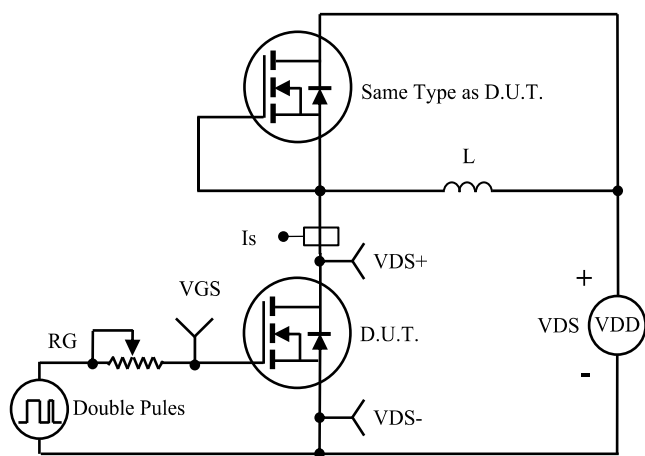


Fig.15- Inductive Switching Test Circuit & Waveform

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Test Circuit & Waveform

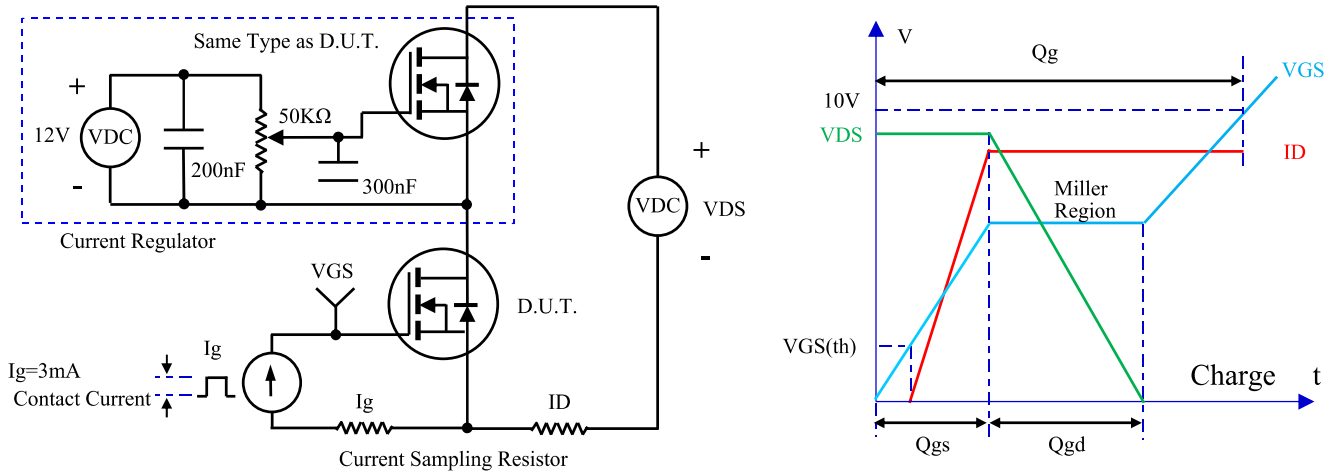


Fig.16- Gate Charge Test Circuit & Waveform

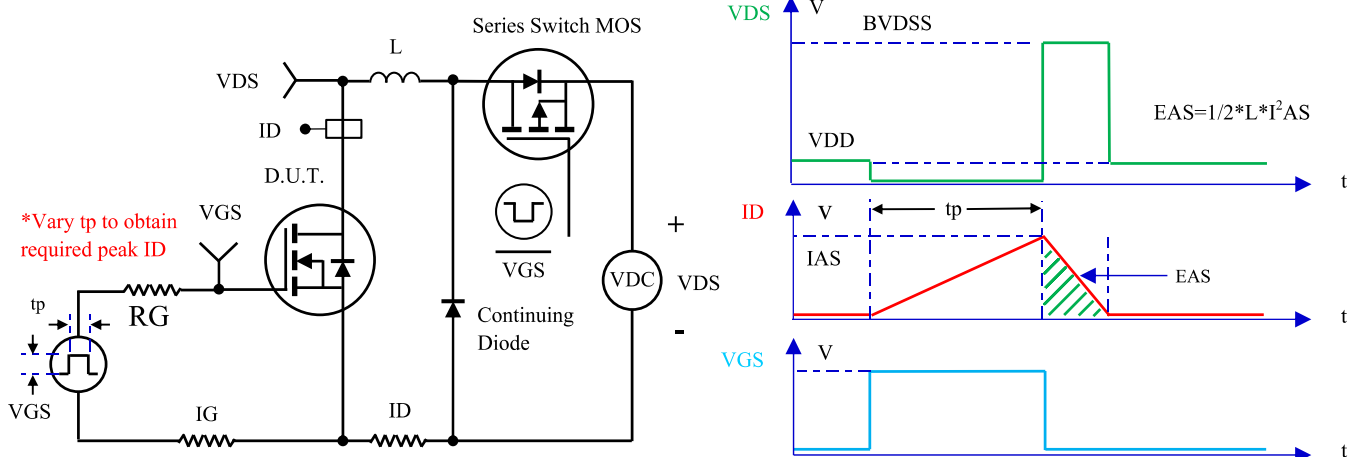


Fig.17- Unclamped Inductive Switching (UIS) Test Circuit & Waveform

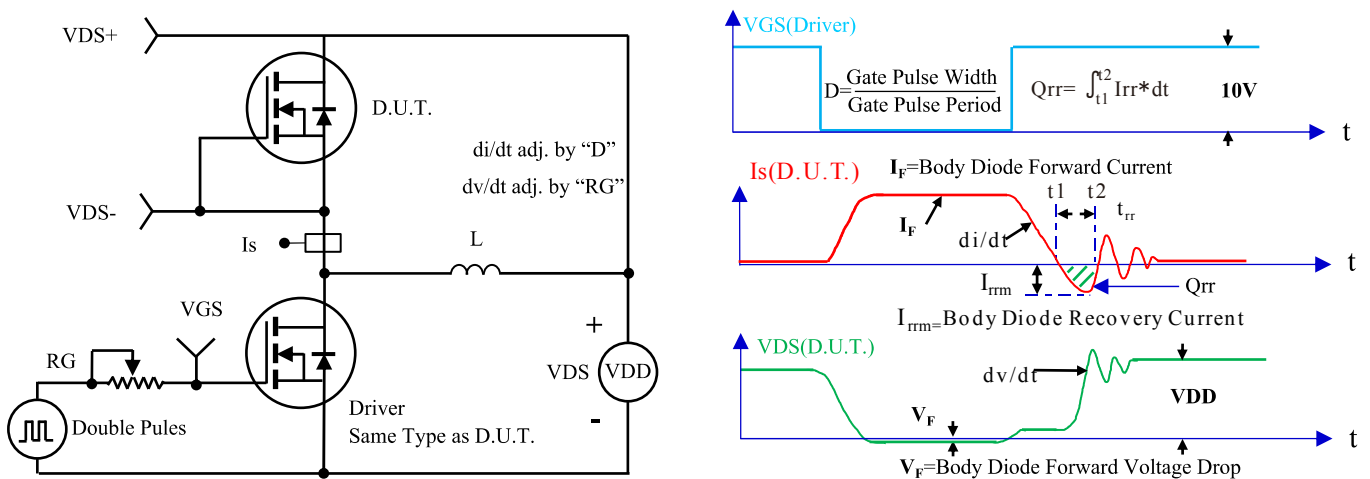


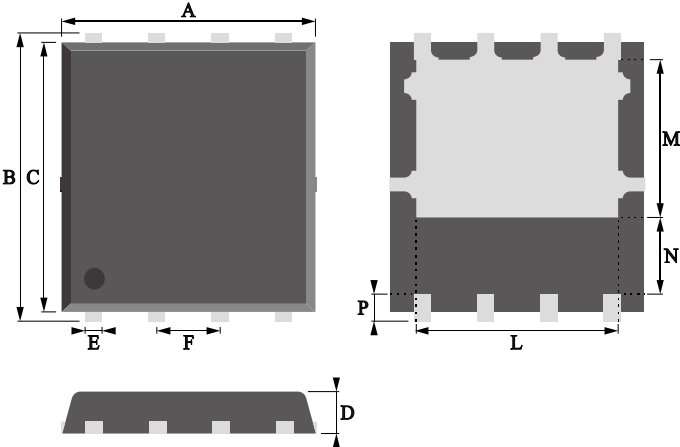
Fig.18- Diode Recovery Test Circuit & Waveform

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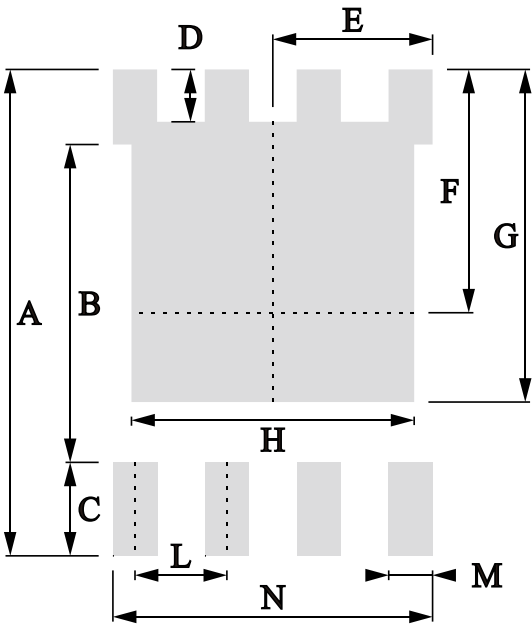
OUTLINE DRAWINGS



PDFN5*6

OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.70	-	5.70	0.1850	-	0.2244
B	5.60	-	6.60	0.2205	-	0.2598
C	5.10	-	6.10	0.2008	-	0.2402
D	0.70	-	1.20	0.0276	-	0.0472
E	0.15	-	0.45	0.0059	-	0.0177
F	1.30	-	1.90	0.0512	-	0.0748
M	3.10	-	3.90	0.1220	-	0.1535
L	3.45	-	4.05	0.1358	-	0.1594
N	1.00	-	1.60	0.0394	-	0.0630
P	0.25	-	0.75	0.0098	-	0.0295

RECOMMEDND LAYOUT DRAWINGS



PDFN5*6

OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	6.61	-	-	0.2602	-
B	-	4.32	-	-	0.1701	-
C	-	1.27	-	-	0.0500	-
D	-	0.71	-	-	0.0280	-
E	-	2.21	-	-	0.0870	-
F	-	3.31	-	-	0.1301	-
G	-	4.52	-	-	0.1780	-
H	-	3.91	-	-	0.1539	-
L	-	1.27	-	-	0.0500	-
M	-	0.61	-	-	0.0240	-
N	-	4.42	-	-	0.1740	-

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MARKING INFORMATION

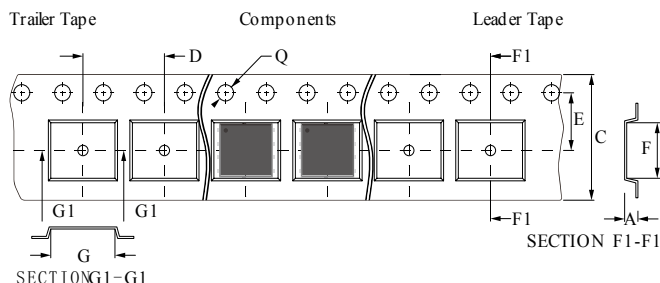


MARKING INSTRUCTIONS

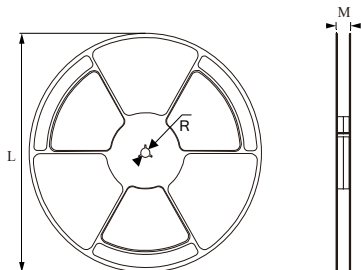
NH=Niuhang Trademark
FF=Product Line Code,According To Actual Changes
YWW=Date Code,According To Actual Changes
LLWWF=Internal Code,According To Actual Changes
NTS580N15P5=Model

PACKAGING

TAPE



REEL



PDFN5*6

OUTLINE DIMENSIONS

Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
TAPE						
A	1.00	-	1.20	0.0394	-	0.0472
C	11.70	-	12.30	0.4606	-	0.4843
D	7.70	-	8.30	0.3031	-	0.3268
E	5.30	-	5.70	0.2087	-	0.2244
F	5.10	-	5.50	0.2008	-	0.2165
G	6.10	-	6.50	0.2402	-	0.2559
Q Φ	1.40	-	1.60	0.0551	-	0.0630
REEL						
L	328.00	-	332.00	12.913	-	13.071
R	12.00	-	14.00	0.4724	-	0.5512
M	16.50	-	18.50	0.6496	-	0.7283

PACKING INFORMATION

Package Type	Package Code	Product Weight Approx(g/Pcs)	Package Method	Quantity (Pcs/Min. Pack.)	Quantity (Pcs/Inner Box)	Quantity (Pcs/Carton)
PDFN5*6	P1	0.087	13" Reel	5000	10000	50000

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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow

	Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
	Average ramp-up rate (T _{Smax} to T _P)	3°C/second max.	3°C/second max.
	Preheat-Temperature Min (T _S min) -Temperature Max (T _S max) -Time(ts min to ts max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
	Time maintained above: -Temperature (T _L) - Time (t _L)	183°C 60-150 seconds	217°C 60-150 seconds
	Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
	Time within 5°C of actual peak temperature (t _p)	10-30 seconds	20-40 seconds
	Ramp down rate	6°C/second max.	6°C/second max.
	Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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- When the appearance of the product and chip size does not change, in order to product the customer. quality, change the internal structure and the production process Niuhang can not notify

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Specification Revision History

Rev.	Date	Changed Items	Pre-Changed Content	Changed Content
A/1	2014-10-20	First Issue		
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